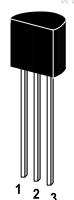
**NPN Silicon Epitaxial Planar Transistor** 

for switching and AF amplifier applications.

The transistor is subdivided into one group according to it DC current gain. As complementary type the PNP transistor ST 2N5086 and ST 2N5087 are recommended.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Base 3. Collector

TO-92 Plastic Package Weight approx. 0.19g

### Absolute Maximum Ratings ( $T_a = 25$ °C)

Parameter	Symbol	Value	Unit	
Collector Base Voltage	V <sub>CBO</sub>	35	V	
Collector Emitter Voltage	V <sub>CEO</sub>	30	V	
Emitter Base Voltage	$V_{EBO}$	4.5	V	
Collector Current	I <sub>C</sub>	50	mA	
Power Dissipation	P <sub>tot</sub>	500	mW	
Junction Temperature	Tj	150	°C	
Storage Temperature Range	T <sub>S</sub>	-55 to +150	°C	







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# ST 2N5088 / 2N5089

#### Characteristics at T<sub>amb</sub>=25 °C

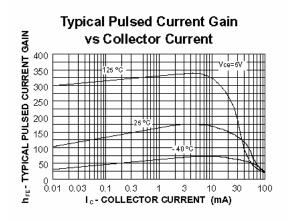
Parameter	·	Symbol	Min.	Тур.	Max.	Unit
DC Current Gain						
at $V_{CE}$ =5V, $I_{C}$ =0.1mA	ST 2N5088	h <sub>FE</sub>	300	-	900	-
	ST 2N5089	h <sub>FE</sub>	400	-	1200	-
at $V_{CE}$ =5V, $I_{C}$ =1mA	ST 2N5088	h <sub>FE</sub>	300	-	-	-
	ST 2N5089	h <sub>FE</sub>	400	-	-	-
at $V_{CE}$ =5V, $I_{C}$ =10mA	ST 2N5088	h <sub>FE</sub>	300	-	-	-
	ST 2N5089	h <sub>FE</sub>	400	_	-	-
Collector Base Breakdown Voltage at I <sub>C</sub> =100µA		\/	35	-	-	V
		$V_{(BR)CBO}$				
Collector Emitter Breakdown Voltage at I <sub>C</sub> =1mA		\/	30	-	-	V
		$V_{(BR)CEO}$				
Emitter Base Breakdown Voltage at I <sub>E</sub> =10µA		\/	4.5	-	-	V
		$V_{(BR)EBO}$				
Collector Cutoff Current at V <sub>CB</sub> =35V		1	-	-	0.05	μA
		I <sub>CBO</sub>				
Emitter Cutoff Current at V <sub>EB</sub> =4.5V		1	-	-	0.05	μA
		I <sub>EBO</sub>				
Collector Saturation Voltage at I <sub>C</sub> =10mA, I <sub>B</sub> =1mA		V <sub>CE(sat)</sub>	-	-	0.5	V
▼ BE(on)						
Gain Bandwidth Product at $V_{CE}$ =5V, $I_{C}$ =0.5mA		f⊤	50	180	1	MHz
		IT.				
Output Capacitance at V <sub>CB</sub> =10V, f=1MHz		СОВ	-	-	4	pF
		ООВ				
Noise Figure		NF			3	dB
at $V_{CE}$ =6V, $I_{C}$ =0.3mA, f=100Hz, $R_{S}$ =10K $\Omega$		INF	-	-	J	uБ

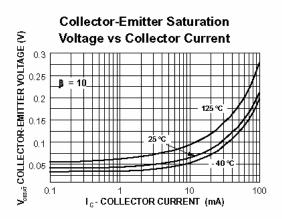


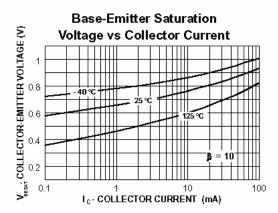


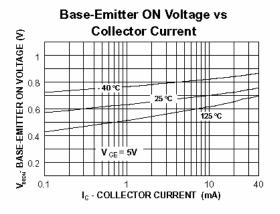


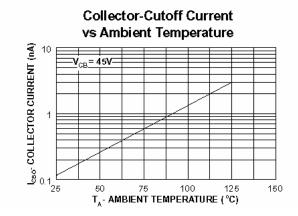














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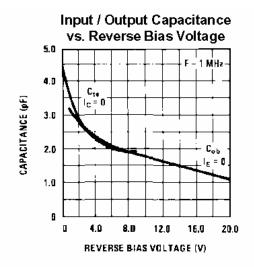


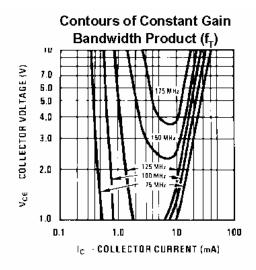


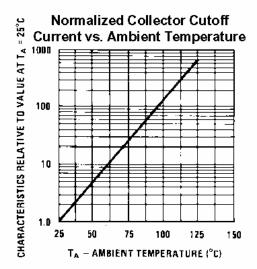


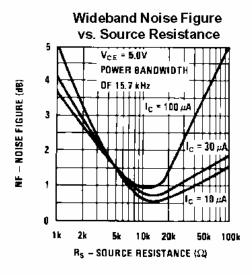
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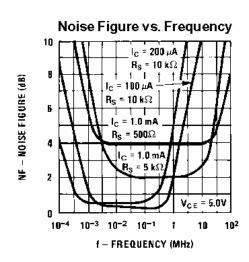
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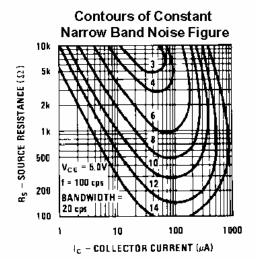














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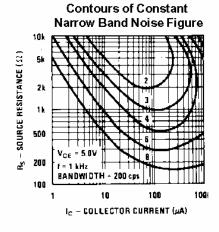


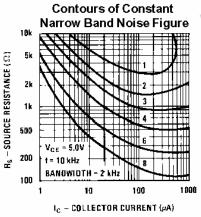


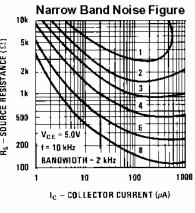


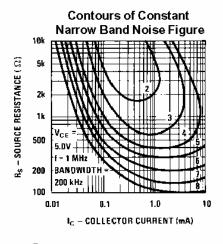
8 16949 : 2002 ISO 14001:2004 ISO 9001:2009 cate No. 05103 Certificate No. WWW. Data Sheet 4U.com

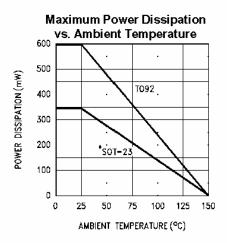
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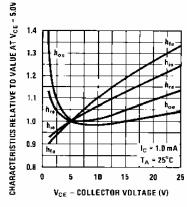


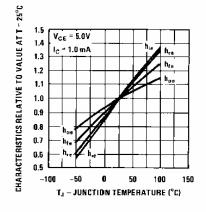


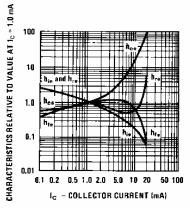














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